



#### **UPDATED 05/08/2008**

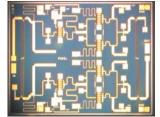
## 17.0 - 20.0 GHz Power Amplifier MMIC

## **FEATURES**

- 17.0 20.0 GHz Operating Frequency Range
- 29.0dBm Output Power at 1dB Compression
- 15.0 dB Typical Small Signal Gain
- -40dBc OIMD3 @Each Tone Pout 19.5dBm

## **APPLICATIONS**

- Point-to-point and point-to-multipoint radio
- Military Radar Systems



Dimension: 2100um x 2650um Thickness: 75um ± 13um



Caution! ESD sensitive device.

## ELECTRICAL CHARACTERISTICS (T<sub>a</sub> = 25 °C, 50 ohm, VDD=7V, IDQ=760mA)

SYMBOL	PARAMETER/TEST CONDITIONS	MIN	TYP	MAX	UNITS
F	Operating Frequency Range	17.0		20.0	GHz
P1dB	Output Power at 1dB Gain Compression	28.0	29.0		dBm
Gss	Small Signal Gain	12.0	15.0		dB
OIMD3	Output 3 <sup>rd</sup> Order Intermodulation Distortion @∆f=10MHz, Each Tone Pout 19.5dBm		-40	-37	dBc
Input RL	Input Return Loss		-15	-10	dB
Output RL	Output Return Loss		-15	-10	dB
ldss	Saturate Drain Current V <sub>DS</sub> =3V, V <sub>GS</sub> =0V	858	1072	1286	mA
V <sub>DD</sub>	Power Supply Voltage		7	8	V
Rth	Thermal Resistance (Au-Sn Eutectic Attach)		9		°C/W
Tb	Operating Base Plate Temperature	-35		+85	°C

# ABSOLUTE MAXIMUM RATINGS FOR CONTINUOUS OPERATION1,2

SYMBOL	CHARACTERISTIC	VALUE
$V_{DS}$	Drain to Source Voltage	8 V
$V_{GS}$	Gate to Source Voltage	-4 V
$I_{DD}$	Drain Current	ldss
$I_GSF$	Forward Gate Current	15mA
$P_{IN}$	Input Power	@ 3dB compression
$T_CH$	Channel Temperature	150°C
$T_{STG}$	Storage Temperature	-65/150°C
$P_T$	Total Power Dissipation	12.6W

<sup>1.</sup> Operating the device beyond any of the above rating may result in permanent damage.

<sup>2.</sup> Bias conditions must also satisfy the following equation  $V_{DS}^*I_{DS} < (T_{CH} - T_{HS})/R_{TH}$ ; where  $T_{HS}$  = ambient temperature

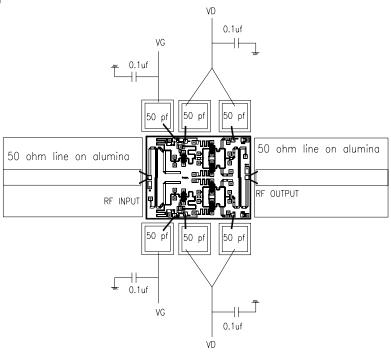




#### **UPDATED 05/08/2008**

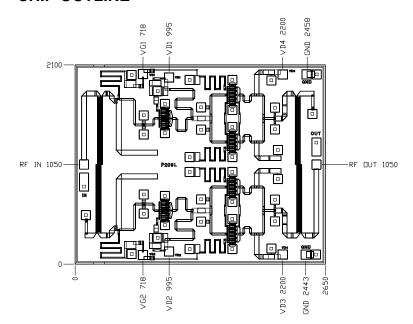
# 17.0 – 20.0 GHz Power Amplifier MMIC

## **Assembly Drawing**



The length of RF wires should be as short as possible. Use at least two wires between RF pad and 50 ohm line and separate the wires to minimize the mutual inductance.

## **CHIP OUTLINE**



Chip Size 2100 x 2650 microns Chip Thickness:  $75 \pm 13$  microns PAD Dimensions: 100 x 100 microns All Dimensions in Microns

Specifications are subject to change without notice.



# **EMP209**

#### **UPDATED 05/08/2008**

## 17.0 – 20.0 GHz Power Amplifier MMIC

### **DISCLAIMER**

EXCELICS SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. EXCELICS DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN.

#### LIFE SUPPORT POLICY

EXCELICS SEMICONDUCTOR PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF EXCELICS SEMICONDUCTOR, INC.

### AS HERE IN:

- 1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, or (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in significant injury to the user.
- 2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.